



InGaN/GaN Blue Chip (15mil)

Device No. : MOC15A465
MOC15A467

Scope

- The specification applies to InGaN LED chips

Structure

- InGaN/GaN Blue Chip
- Bond pad P(anode) pad : Au
N(cathode) pad : Au

Size

- Chip size : $360\mu\text{m} \times 420\mu\text{m}$
- Chip Thickness : $110\mu\text{m}$
- Measurement tolerance $\pm 10\mu\text{m}$
- Pattern drawing : per fig.1

Electro-Optical Characteristics

Parameter	Symbol	Condition	Min.	Typ.	Max.	Unit
Forward Voltage	V_F	$I_F = 20\text{mA}$	2.9	3.4	3.8	V
Reverse Current	I_R	$V_R = 5\text{V}$	--	--	2	μA
Luminous Intensity	I_V	$I_F = 20\text{mA}$	※	※	※	mcd
Wavelength	λ_D	$I_F = 20\text{mA}$	465	--	470	nm

The measurements base on chip on wafer form.

※ Rank K: 80~90, Rank L: 90~100, Rank M: 100~120,

※ Rank O: 120~140 , Rank Q: 140~160, Rank Q: 160~180, Rank U: 180 ↑

fig. 1 (unit: μm)

